# 2.5V Drive Pch MOS FET RTM002P02

#### Structure

Silicon P-channel MOS FET

#### Features

- 1) Low On-resistance.
- 2) Small package (VMT3).
- 3) 2.5V drive.

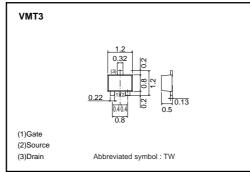
#### Applications

Switching

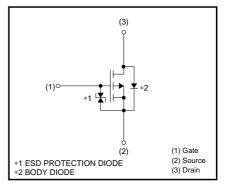
#### Packaging specifications

	Package	Taping	
Туре	Code	T2L	
	Basic ordering unit (pieces)	8000	
RTM002P02		0	

#### •External dimensions (Unit : mm)



#### Inner circuit



#### •Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit		
Drain-source voltage		VDSS	-20	V		
Gate-source voltage		Vgss	±12	V		
Drain ourrent	Continuous	ID	±0.2	А		
Drain current	Pulsed	I <sub>DP</sub> *1	±0.4	А		
Total power dissipation		P <sub>D</sub> *2	0.15	W		
Channel temperature		Tch	150	°C		
Range of storage temperature		Tstg	-55 to +150	°C		

\*1 Pw≤10µs, Duty cycle≤1%

\*2 Each terminal mounted on a recommended land

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#### •Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	833	°C/W

\* Each terminal mounted on a recommended land

# Transistors

# •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	±10	μA	Vgs= ±12V, Vds=0V
Drain-source breakdown voltage	V(BR) DSS	-20	-	_	V	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	-	-1	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> =0V
Gate threshold voltage	VGS (th)	-0.7	-	-2.0	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	RDS (on)*	-	1.0	1.5	Ω	I <sub>D</sub> = -0.2A, V <sub>GS</sub> = -4.5V
		-	1.1	1.6	Ω	I <sub>D</sub> = -0.2A, V <sub>GS</sub> = -4V
		-	2.0	3.0	Ω	I <sub>D</sub> = -0.15A, V <sub>GS</sub> = -2.5V
Forward transfer admittance	Y <sub>fs</sub> *	0.2	-	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.15A
Input capacitance	Ciss	-	50	_	pF	V <sub>DS</sub> =-10V
Output capacitance	Coss	-	5	_	pF	V <sub>GS</sub> = 0V
Reverse transfer capacitance	Crss	-	5	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	9	-	ns	Vdd≒-15V
Rise time	tr *	_	6	_	ns	$I_{D} = -0.15A$
Turn-off delay time	t <sub>d (off)</sub> *	-	35	-	ns	VGs= –4.5V R∟= 100Ω
Fall time	t <sub>f</sub> *	_	45	_	ns	$R_{G}=10\Omega$

\*Pulsed

# •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	-1.2	V	Is= -0.1A, V <sub>GS</sub> =0V

# rohm

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